2SB0947 (2SB947), 2SB0947A (2SB947A)

Silicon PNP epitaxial planar type

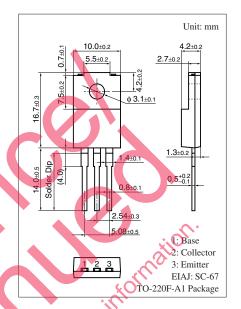
For low-voltage switcing

■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-base voltage	2SB0947	V _{CBO}	-40	V	
(Emitter open)	2SB0947A		-50		
Collector-emitter voltage	2SB0947	V _{CEO}	-20	V	
(Base open)	2SB0947A		-40		
Emitter-base voltage (Collector open)		V _{EBO}	-5	V	
Collector current	I_{C}	-10	A		
Peak collector current	I_{CP}	-15	A		
Collector power		P _C	35	W	
dissipation	$T_a = 25^{\circ}C$		2		
Junction temperature	3	T_{j}	150	°C	
Storage temperature		T_{stg}	-55 to +1 50	°C	



■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage 2SF	30947 V _{CEO}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-20			V
(Base open) 2SE	80947A	7, 20,	-40			
Collector-base cutoff 2SF	30947 I _{CBO}	$V_{\rm CB} = -40 \text{ V. } I_{\rm E} = 0$			-50	μΑ
current (Emitter open) 2SE	30947A	$V_{CB} = -50 \text{ V}, I_E = 0$			-50	
Emitter-base cutoff current (Collector	open) I _{EBO}	$V_{ER} = -5 \text{ V}, I_C = 0$			-50	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -2 V, I_{C} = -0.1 A$	45			_
	h _{FE2} *	$V_{CE} = -2 V, I_C = -2 A$	60		260	
Collector-emitter saturation volta	age V _{CE(sat)}	$I_C = -7 \text{ A}, I_B = -0.23 \text{ A}$			- 0.6	V
Base-emitter saturation voltage	BE(sat)	$I_C = -7 \text{ A}, I_B = -0.23 \text{ A}$			-1.5	V
Transition frequency	f_{T}	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		200		pF
(Common base, input open circu	ited)					
Turn-on time	t _{on}	$I_C = -2 \text{ A}, I_{B1} = -66 \text{ mA}, I_{B2} = 66 \text{ mA}$		0.1		μs
Storage time	t _{stg}	$V_{CC} = -20 \text{ V}$		0.5		μs
Fall time	$t_{\rm f}$			0.1		μs

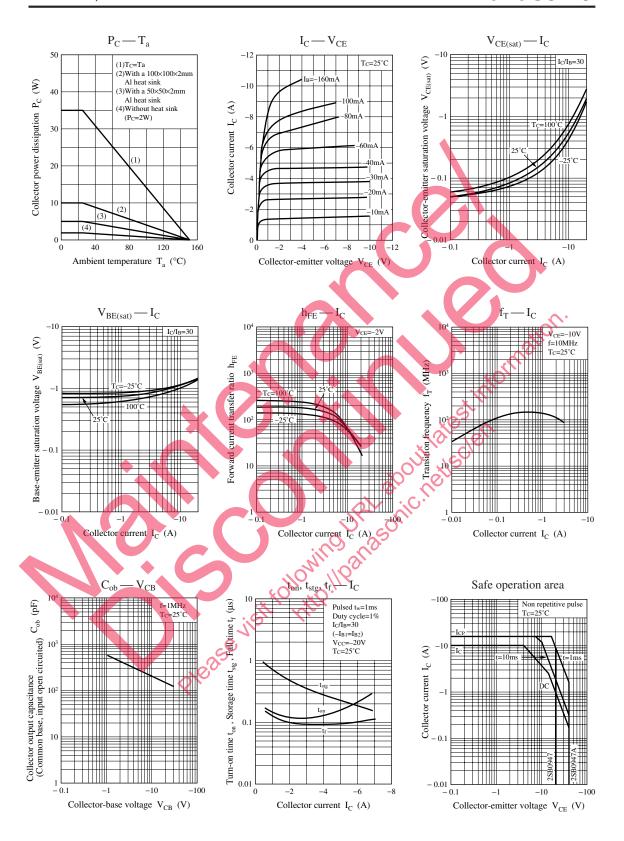
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	Q	Р	
h_{FE2}	60 to 120	90 to 180	130 to 260	

Note) The part numbers in the parenthesis show conventional part number.

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